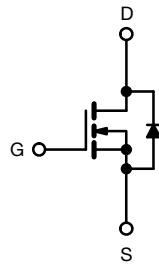
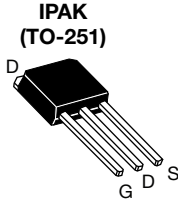


E Series Power MOSFET



N-Channel MOSFET

FEATURES

- Low figure-of-merit (FOM) $R_{on} \times Q_g$
- Low effective capacitance (C_{iss})
- Reduced switching and conduction losses
- Ultra low gate charge (Q_g)
- Avalanche energy rated (UIS)
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Server and telecom power supplies
- Switch mode power supplies (SMPS)
- Power factor correction power supplies (PFC)
- Lighting
 - High-intensity discharge (HID)
 - Fluorescent ballast lighting
- Industrial
 - Welding
 - Induction heating
 - Motor drives
 - Battery chargers
 - Renewable energy
 - Solar (PV inverters)

PRODUCT SUMMARY

| | | |
|---|-----------------|------|
| V_{DS} (V) at T_J max. | 850 | |
| $R_{DS(on)}$ typ. (Ω) at 25 °C | $V_{GS} = 10$ V | 1.25 |
| Q_g max. (nC) | 16.5 | |
| Q_{gs} (nC) | 3 | |
| Q_{gd} (nC) | 5 | |
| Configuration | Single | |

ORDERING INFORMATION

| | |
|---------------------------------|----------------|
| Package | IPAK (TO-251) |
| Lead (Pb)-free and halogen-free | SiHU4N80AE-GE3 |


ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

| PARAMETER | SYMBOL | LIMIT | UNIT |
|---|------------------|----------------|------|
| Drain-source voltage | V_{DS} | 800 | V |
| Gate-source voltage | V_{GS} | ± 30 | |
| Continuous drain current ($T_J = 150$ °C) | V_{GS} at 10 V | $T_C = 25$ °C | A |
| | | $T_C = 100$ °C | |
| Pulsed drain current ^a | I_{DM} | 7.0 | |
| Linear derating factor | | 0.5 | W/°C |
| Single pulse avalanche energy ^b | E_{AS} | 6.9 | mJ |
| Maximum power dissipation | P_D | 62.5 | W |
| Operating junction and storage temperature range | T_J, T_{stg} | -55 to +150 | °C |
| Drain-source voltage slope | dv/dt | $T_J = 125$ °C | V/ns |
| Reverse diode dv/dt ^d | | 0.2 | |
| Soldering recommendations (peak temperature) ^c | For 10 s | 260 | °C |

Notes

- Repetitive rating; pulse width limited by maximum junction temperature
- $V_{DD} = 140$ V, starting $T_J = 25$ °C, $L = 28.2$ mH, $R_g = 25$ Ω , $I_{AS} = 0.7$ A
- 1.6 mm from case
- $I_{SD} \leq I_D$, $di/dt = 100$ A/ μ s, starting $T_J = 25$ °C

| THERMAL RESISTANCE RATINGS | | | | |
|----------------------------------|------------|------|------|------|
| PARAMETER | SYMBOL | TYP. | MAX. | UNIT |
| Maximum junction-to-ambient | R_{thJA} | - | 62 | °C/W |
| Maximum junction-to-case (drain) | R_{thJC} | - | 2.0 | |

| SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted) | | | | | | | |
|---|---------------------|---|---|------|------|-----------|---------------|
| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN. | TYP. | MAX. | UNIT |
| Static | | | | | | | |
| Drain-source breakdown voltage | V_{DS} | $V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$ | | 800 | - | - | V |
| V_{DS} temperature coefficient | $\Delta V_{DS}/T_J$ | Reference to $25\text{ }^\circ\text{C}$, $I_D = 1\text{ mA}$ | | - | 0.8 | - | V/°C |
| Gate-source threshold voltage (N) | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$ | | 2.0 | - | 4.0 | V |
| Gate-source leakage | I_{GSS} | $V_{GS} = \pm 20\text{ V}$ | | - | - | ± 100 | nA |
| | | $V_{GS} = \pm 30\text{ V}$ | | - | - | ± 10 | μA |
| Zero gate voltage drain current | I_{DSS} | $V_{DS} = 800\text{ V}, V_{GS} = 0\text{ V}$ | | - | - | 1 | μA |
| | | $V_{DS} = 640\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$ | | - | - | 10 | |
| Drain-source on-state resistance | $R_{DS(on)}$ | $V_{GS} = 10\text{ V}$ | $I_D = 1.0\text{ A}$ | - | 1.25 | 1.44 | Ω |
| Forward transconductance ^a | g_{fs} | $V_{DS} = 30\text{ V}, I_D = 2\text{ A}$ | | - | 1.1 | - | S |
| Dynamic | | | | | | | |
| Input capacitance | C_{iss} | $V_{GS} = 0\text{ V},$ $V_{DS} = 100\text{ V},$ $f = 1\text{ MHz}$ | | - | 11 | - | pF |
| Output capacitance | C_{oss} | | | - | 3 | - | |
| Reverse transfer capacitance | C_{rss} | | | - | 5 | - | |
| Effective output capacitance, energy related ^a | $C_{o(er)}$ | $V_{DS} = 0\text{ V to } 480\text{ V}, V_{GS} = 0\text{ V}$ | | - | 10 | - | pF |
| Effective output capacitance, time related ^b | $C_{o(tr)}$ | | | - | 65 | - | |
| Total gate charge | Q_g | $V_{GS} = 10\text{ V}$ | $I_D = 2\text{ A}, V_{DS} = 640\text{ V}$ | - | 11 | 16.5 | nC |
| Gate-source charge | Q_{gs} | | | - | 3 | - | |
| Gate-drain charge | Q_{gd} | | | - | 5 | - | |
| Turn-on delay time | $t_{d(on)}$ | $V_{DD} = 640\text{ V}, I_D = 2\text{ A},$ $V_{GS} = 10\text{ V}, R_g = 4.7\text{ }\Omega$ | | - | 11 | 22 | ns |
| Rise time | t_r | | | - | 7 | 14 | |
| Turn-off delay time | $t_{d(off)}$ | | | - | 12 | 24 | |
| Fall time | t_f | | | - | 25 | 50 | |
| Gate input resistance | R_g | $f = 1\text{ MHz}, \text{open drain}$ | | 1.7 | 3.5 | 7.0 | Ω |
| Drain-Source Body Diode Characteristics | | | | | | | |
| Continuous source-drain diode current | I_S | MOSFET symbol showing the integral reverse p-n junction diode  | | - | - | 4.0 | A |
| Pulsed diode forward current | I_{SM} | | | - | - | 7.0 | |
| Diode forward voltage | V_{SD} | $T_J = 25\text{ }^\circ\text{C}, I_S = 2\text{ A}, V_{GS} = 0\text{ V}$ | | - | - | 1.2 | V |
| Reverse recovery time | t_{rr} | $T_J = 25\text{ }^\circ\text{C}, I_F = I_S = 2\text{ A},$ $di/dt = 100\text{ A}/\mu\text{s}, V_R = 25\text{ V}$ | | - | 266 | 532 | ns |
| Reverse recovery charge | Q_{rr} | | | - | 1.1 | 2.2 | μC |
| Reverse recovery current | I_{RRM} | | | - | 6.6 | - | A |

Notes

- a. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 V to 480 V V_{DSS}
 b. $C_{oss(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 V to 480 V V_{DSS}

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

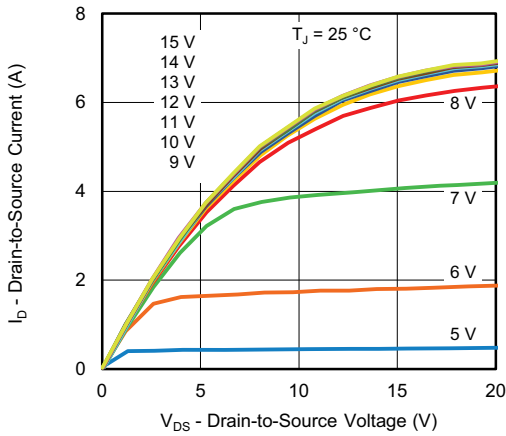


Fig. 1 - Typical Output Characteristics

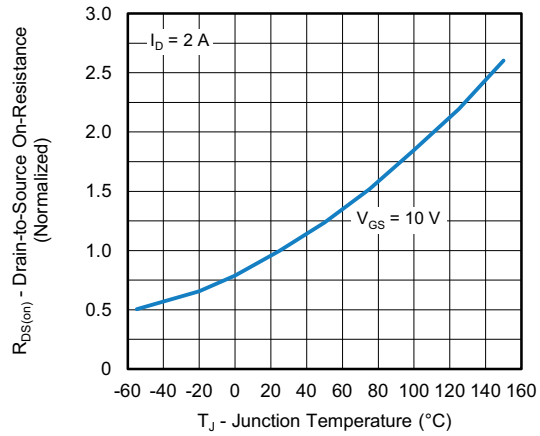


Fig. 4 - Normalized On-Resistance vs. Temperature

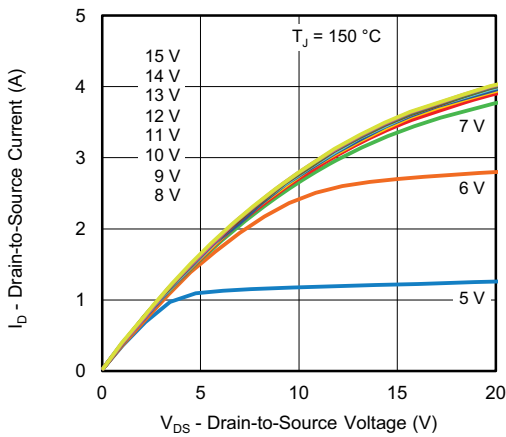


Fig. 2 - Typical Output Characteristics

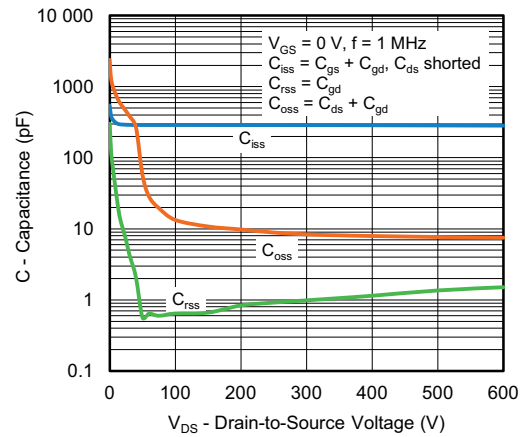


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

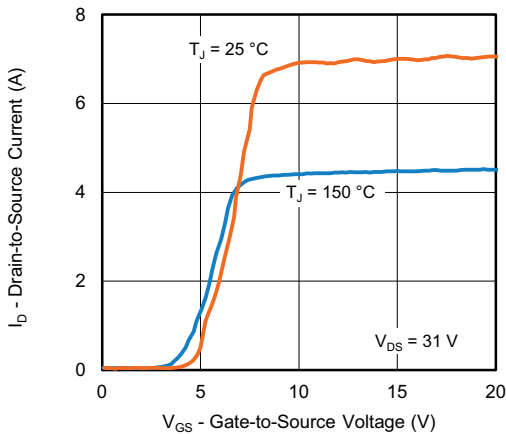


Fig. 3 - Typical Transfer Characteristics

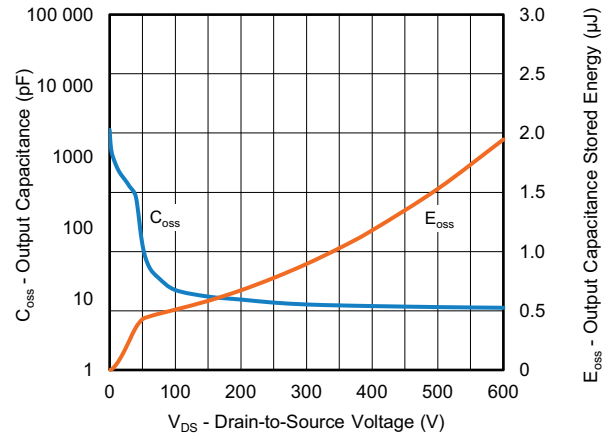


Fig. 6 - C_{oss} and E_{oss} vs. V_{DS}

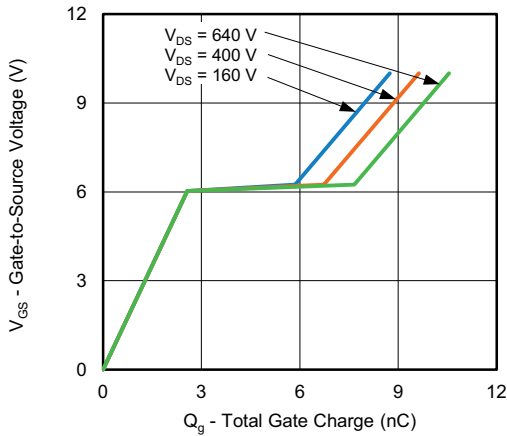


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

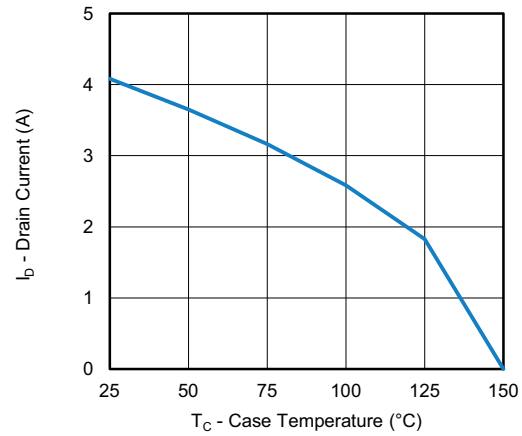


Fig. 10 - Maximum Drain Current vs. Case Temperature

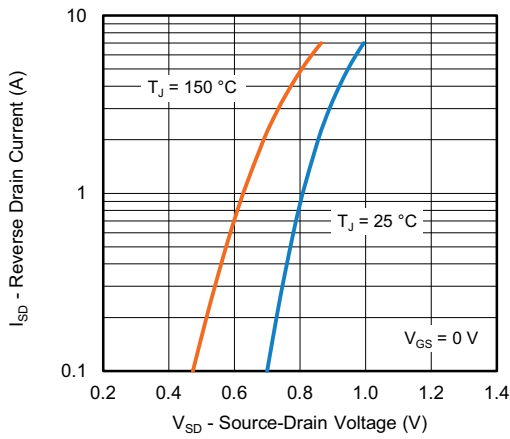


Fig. 8 - Typical Source-Drain Diode Forward Voltage

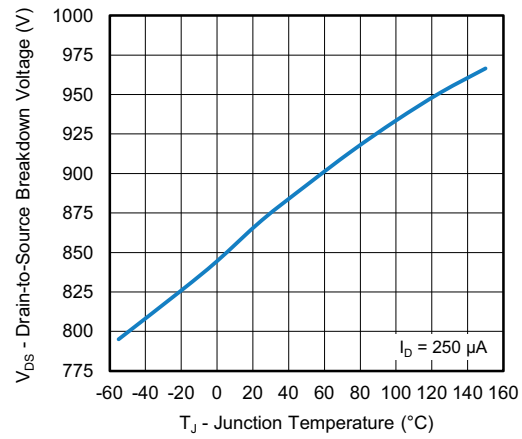


Fig. 11 - Temperature vs. Drain-to-Source Voltage

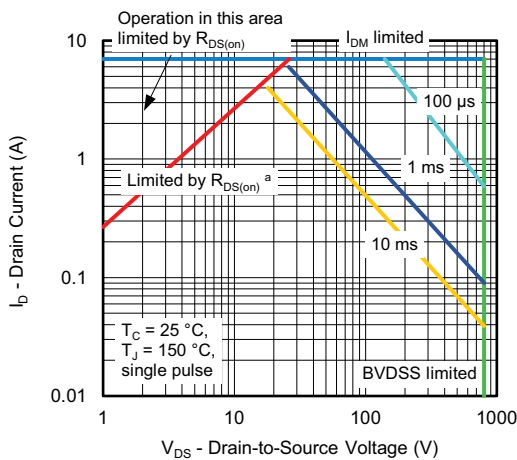


Fig. 9 - Maximum Safe Operating Area

Note

a. $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

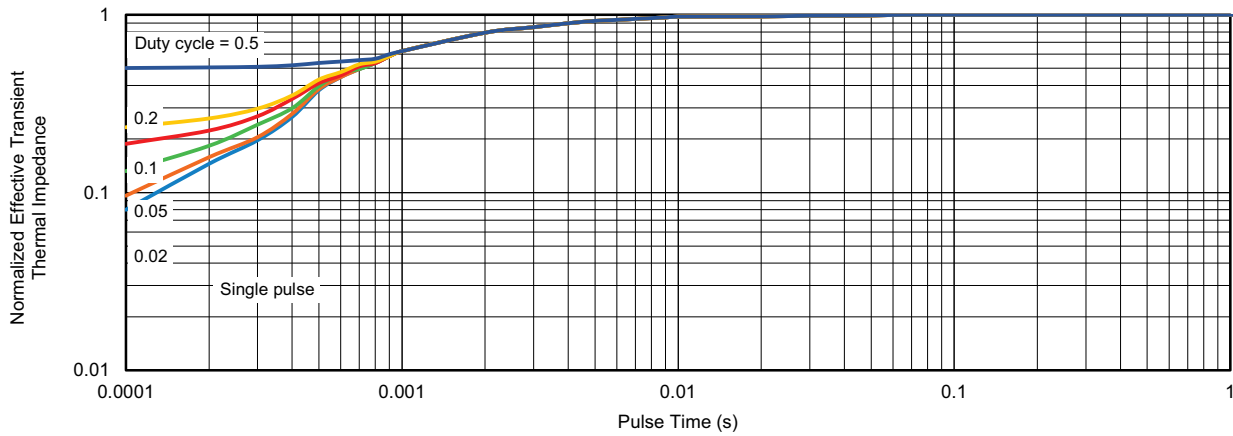


Fig. 12 - Normalized Transient Thermal Impedance, Junction-to-Case

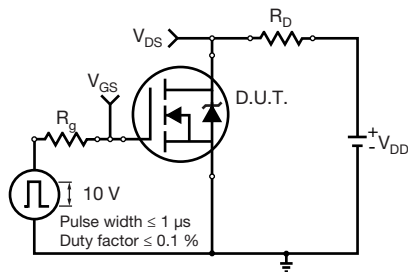


Fig. 13 - Switching Time Test Circuit

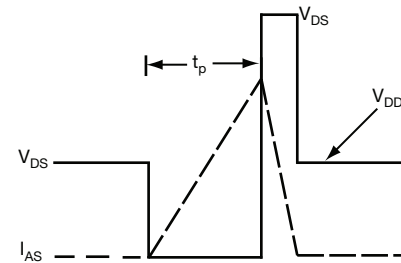


Fig. 16 - Unclamped Inductive Waveforms

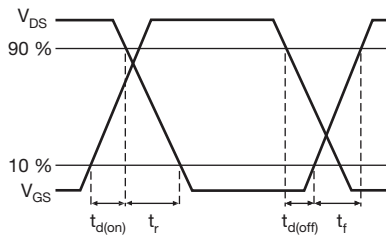


Fig. 14 - Switching Time Waveforms

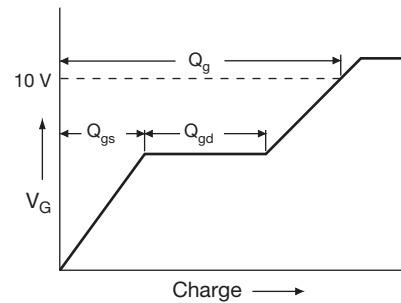


Fig. 17 - Basic Gate Charge Waveform

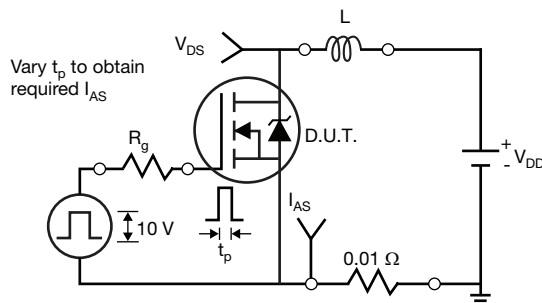


Fig. 15 - Unclamped Inductive Test Circuit

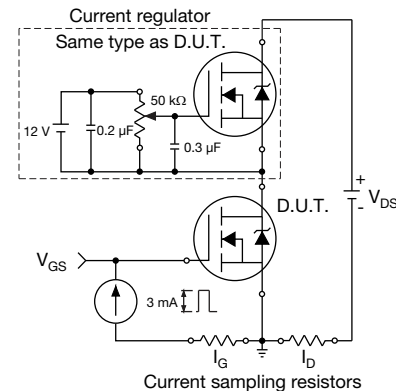
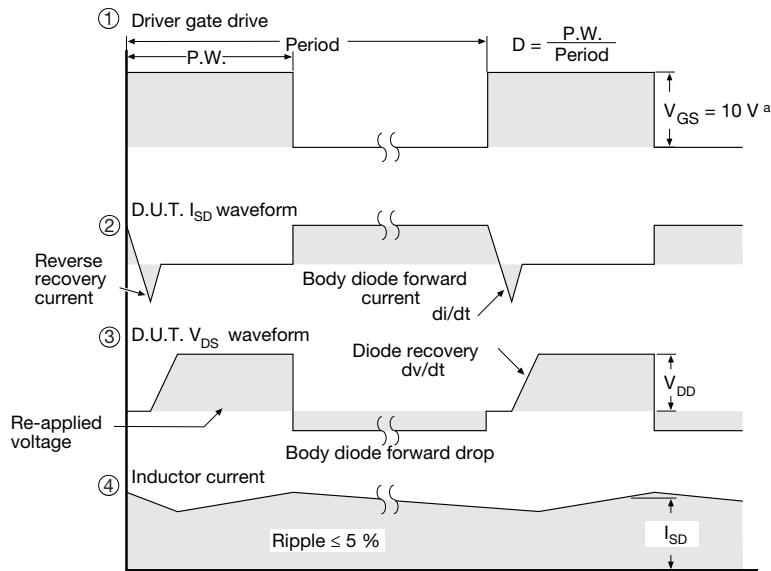
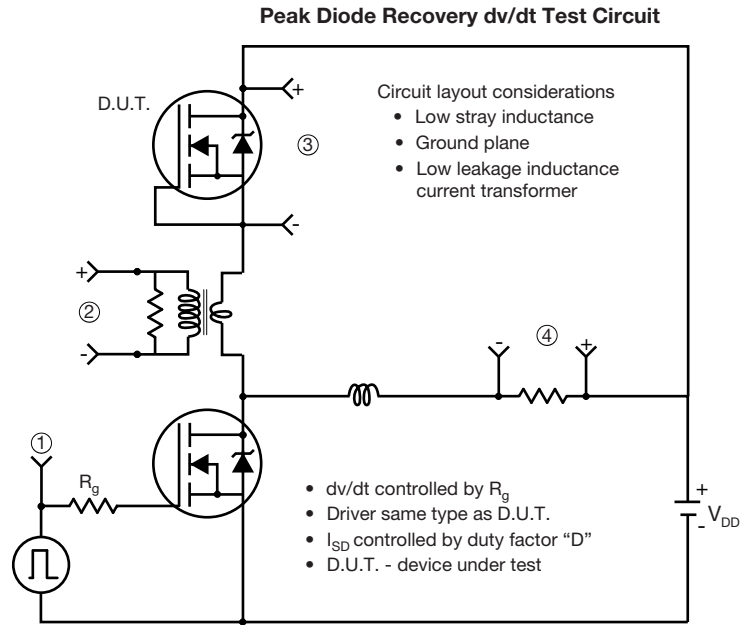


Fig. 18 - Gate Charge Test Circuit



Note
 a. $V_{GS} = 5 V$ for logic level devices

Fig. 19 - For N-Channel

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